



SANYO Semiconductors

# DATA SHEET

An ON Semiconductor Company

## CPH3140 / CPH3240 — PNP / NPN Epitaxial Planar Silicon Transistors High-Voltage Switching Applications

### Features

- Adoption of FBIT, MBIT processes
- High breakdown voltage and large current capacity
- High-speed switching
- Ultrasmall size making it easy to provide high-density, small-sized hybrid ICs

### Specifications ( ) : CPH3140

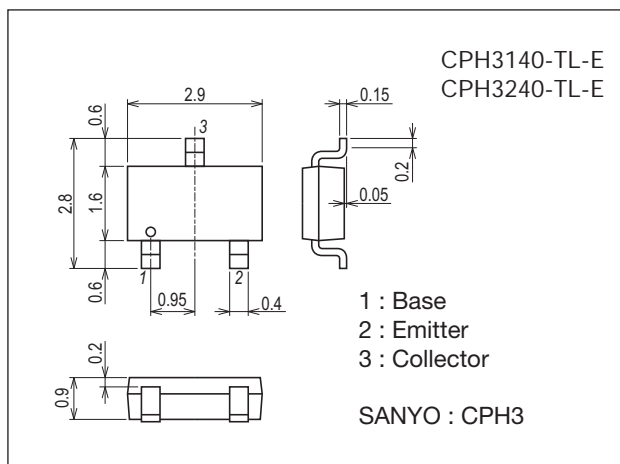
#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CB0</sub>		(-)120	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>		(-)100	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		(-)6	V
Collector Current	I <sub>C</sub>		(-)1	A
Collector Current (Pulse)	I <sub>CP</sub>		(-)2	A
Collector Dissipation	P <sub>C</sub>	When mounted on ceramic substrate (600mm <sup>2</sup> ×0.8mm)	0.9	W
Junction Temperature	T <sub>J</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

### Package Dimensions

unit : mm (typ)

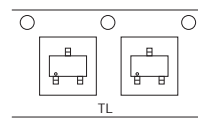
7015A-003



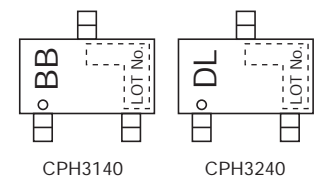
### Product & Package Information

- Package : CPH3
- JEITA, JEDEC : SC-59, TO-236, SOT-23
- Minimum Packing Quantity : 3,000 pcs./reel

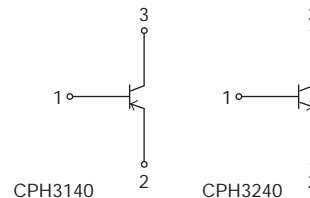
### Packing Type: TL



### Marking



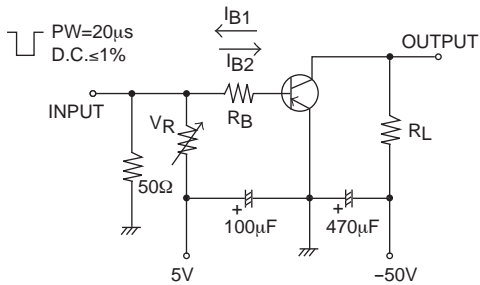
### Electrical Connection



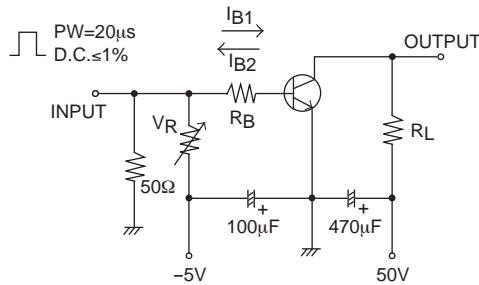
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	ICBO	V <sub>CB</sub> =(-)100V, I <sub>E</sub> =0A			(-)100	nA
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0A			(-)100	nA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)100mA	140		400	
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)100mA		120		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =(-)10V, f=1MHz		(13)8.5		pF
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =(-)400mA, I <sub>B</sub> =(-)40mA		(-0.2)0.1	(-0.6)0.4	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =(-)400mA, I <sub>B</sub> =(-)40mA		(-)0.85	(-)1.2	V
Collector-to-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =(-)10μA, I <sub>E</sub> =0A	(-)120			V
Collector-to-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =(-)1mA, R <sub>BE</sub> =∞	(-)100			V
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =(-)10μA, I <sub>C</sub> =0A	(-)6			V
Turn-On Time	t <sub>on</sub>	See specified Test Circuit.		(80)80		ns
Storage Time	t <sub>stg</sub>			(700)850		ns
Fall Time	t <sub>f</sub>			(40)50		ns

Switching Time Test Circuit



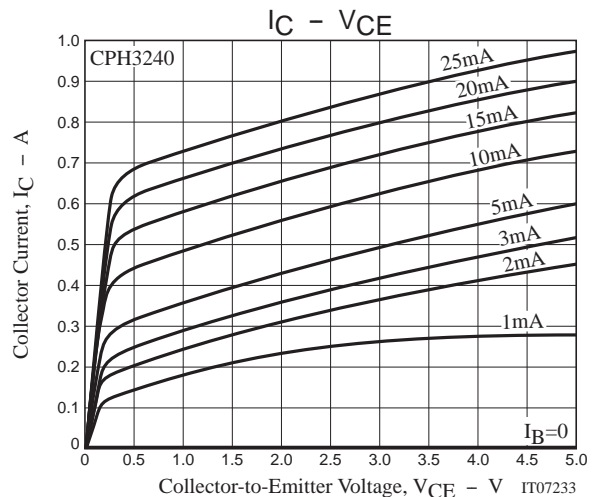
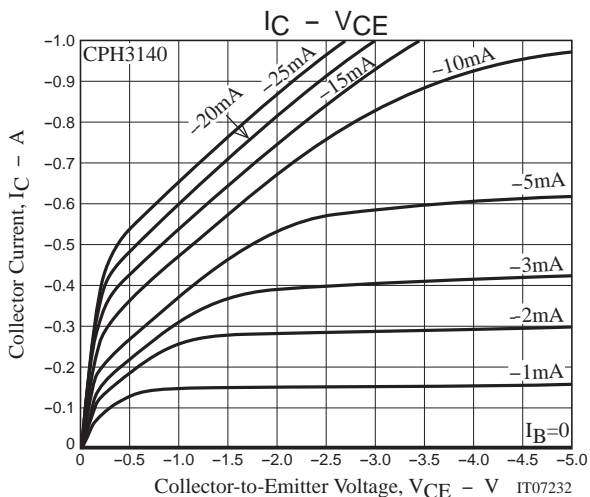
IC = -10IB1 = 10IB2 = -400mA  
CPH3140

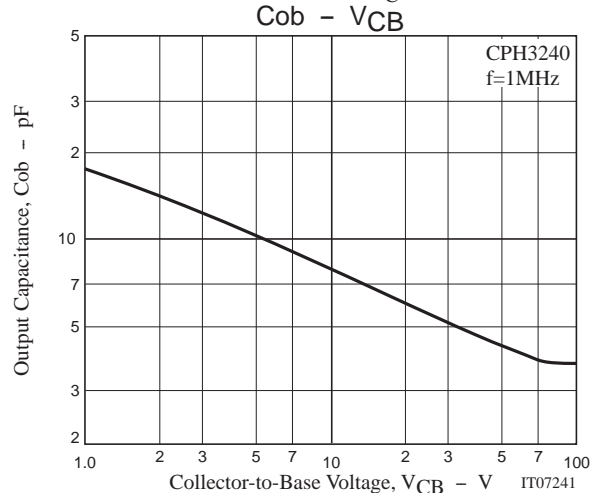
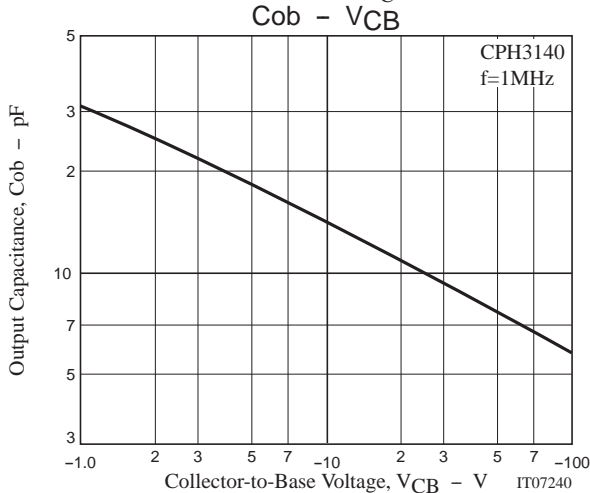
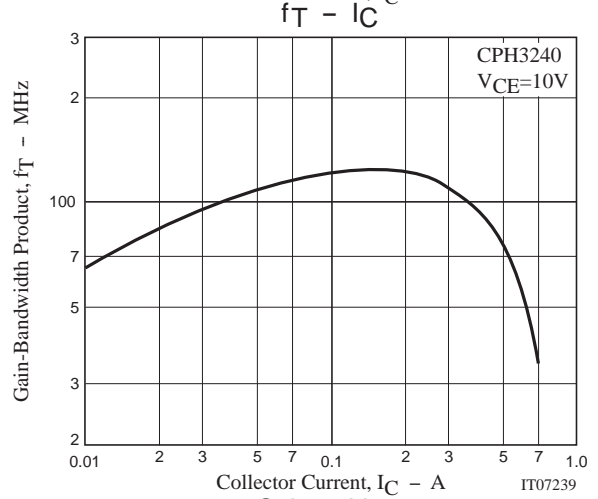
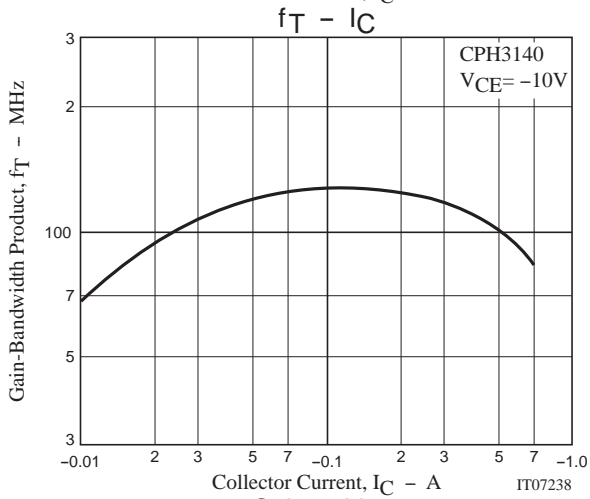
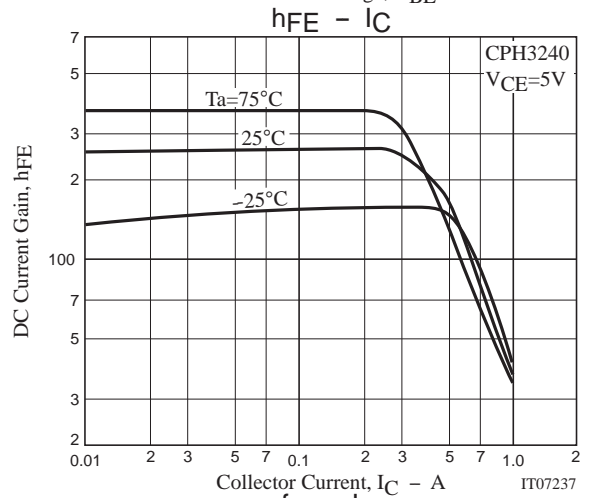
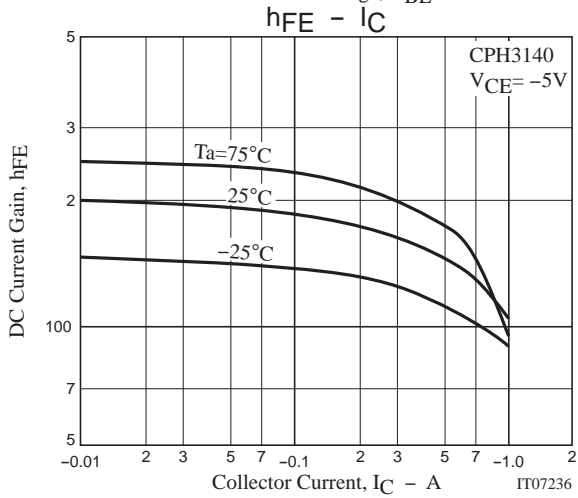
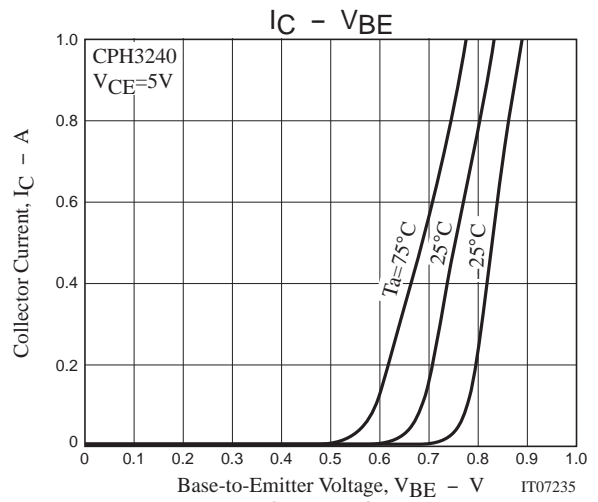
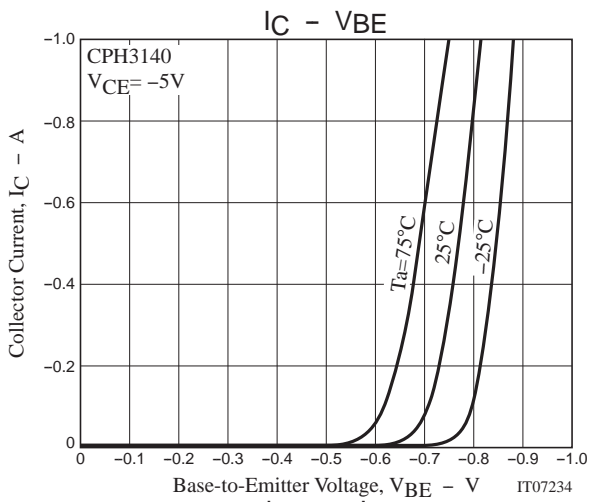


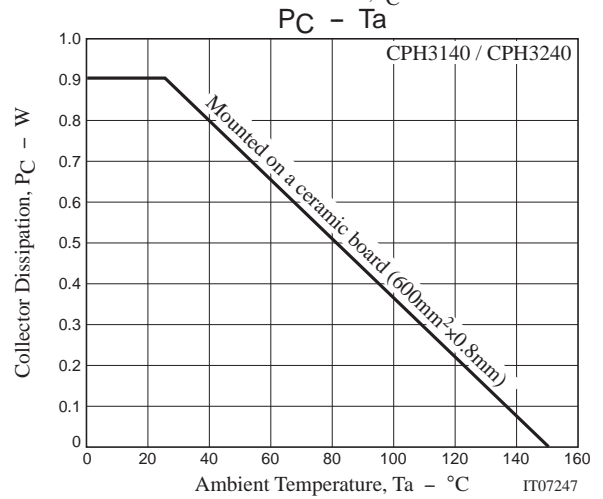
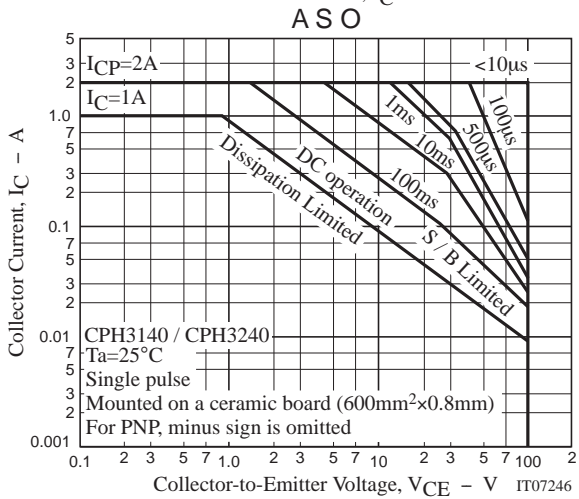
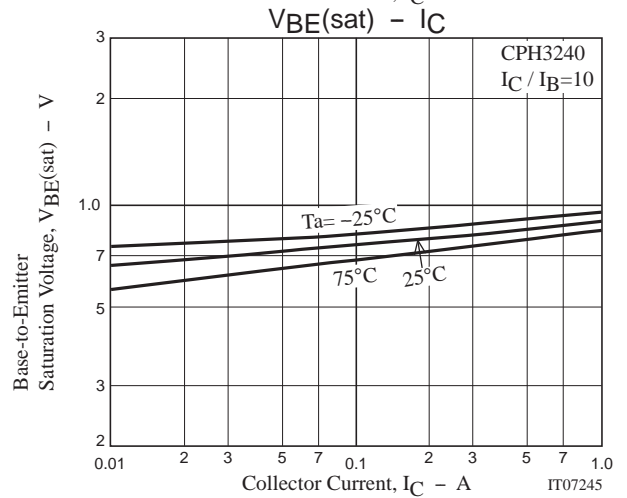
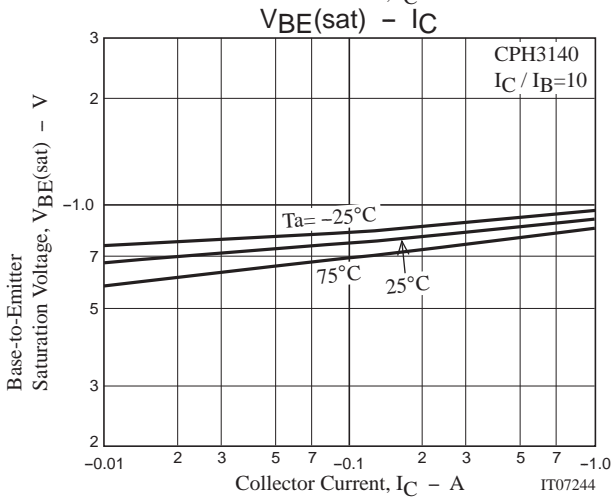
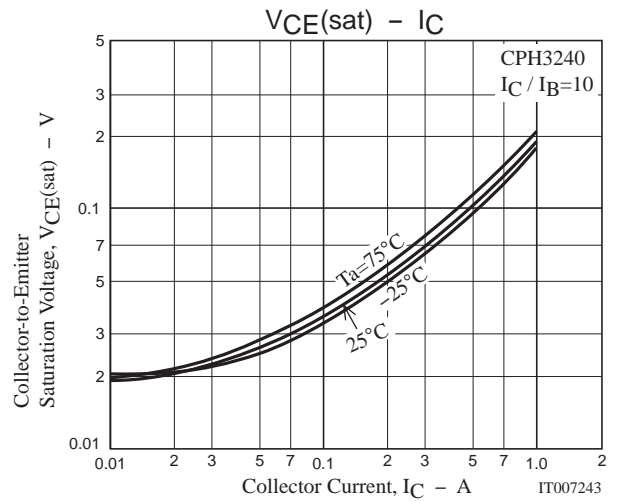
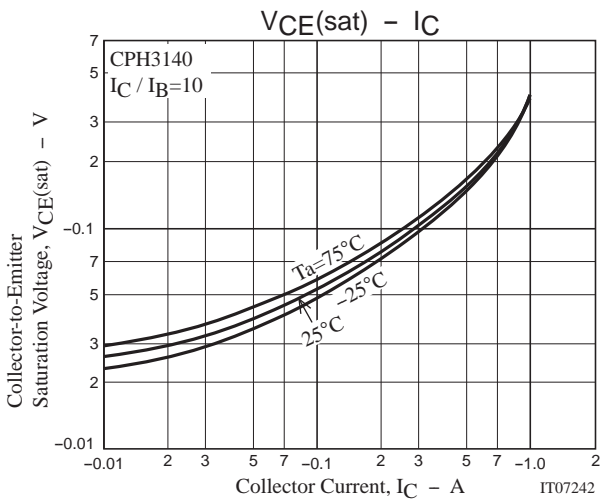
IC = 10IB1 = -10IB2 = 400mA  
CPH3240

Ordering Information

Device	Package	Shipping	memo
CPH3140-TL-E	CPH3	3,000pcs./reel	Pb Free
CPH3240-TL-E	CPH3	3,000pcs./reel	Pb Free





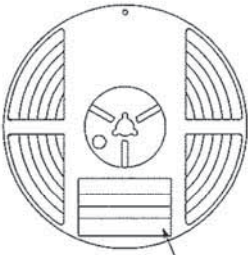


Embossed Taping Specification  
CPH3140-TL-E, CPH3240-TL-E

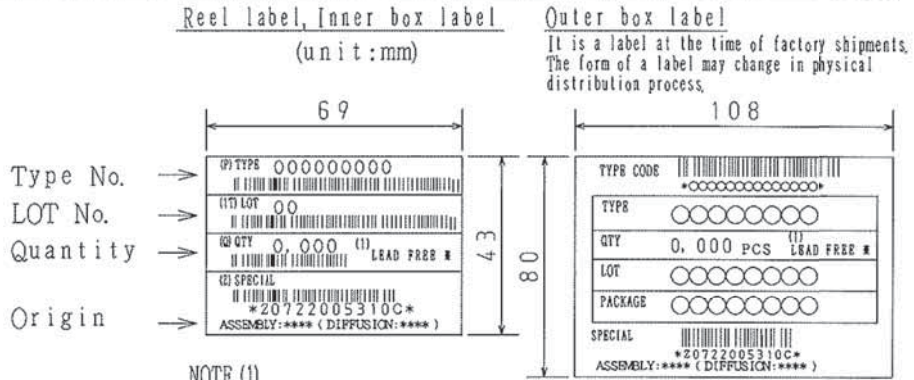
1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
CPH3	CPH3	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



Reel label



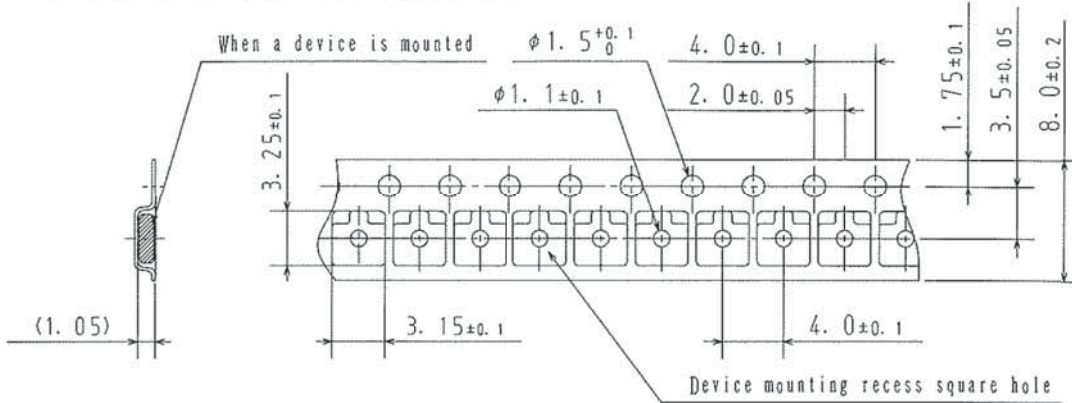
NOTE (1)

The LEAD FREE # description shows that the surface treatment of the terminal is lead free.

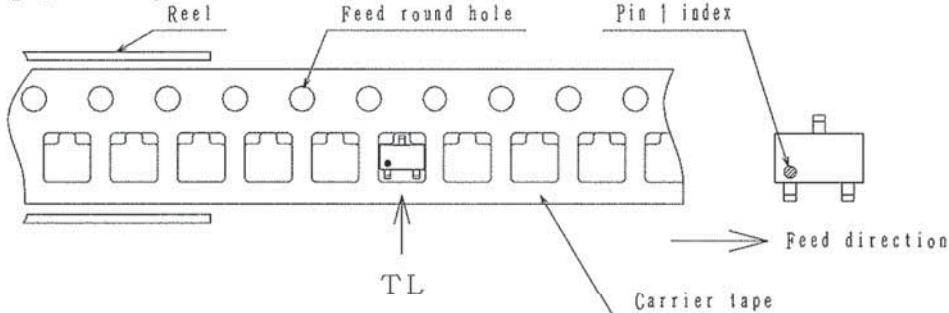
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



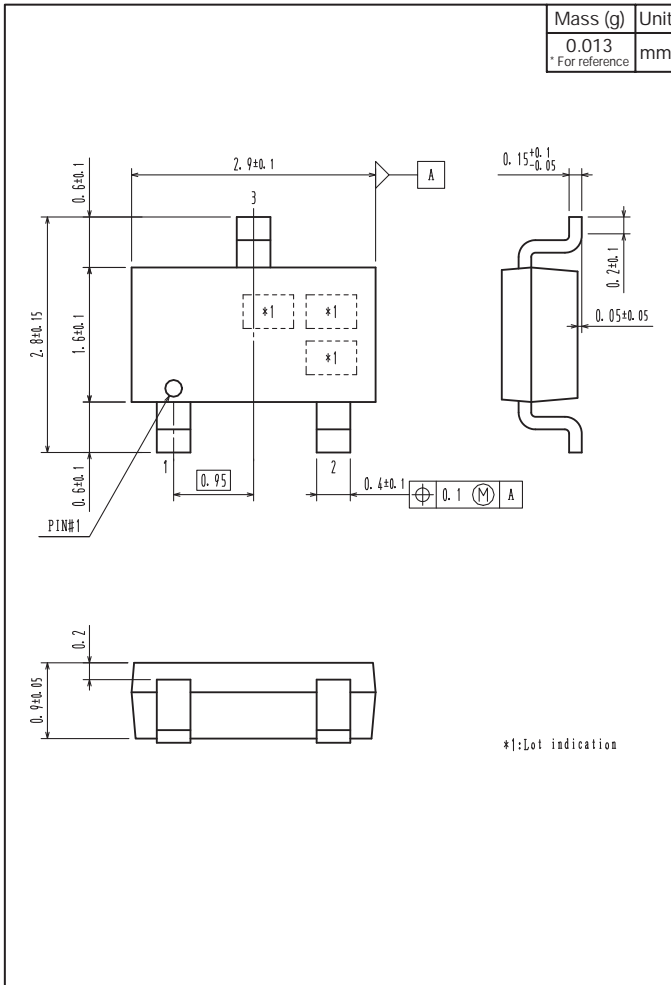
2-2. Device placement direction



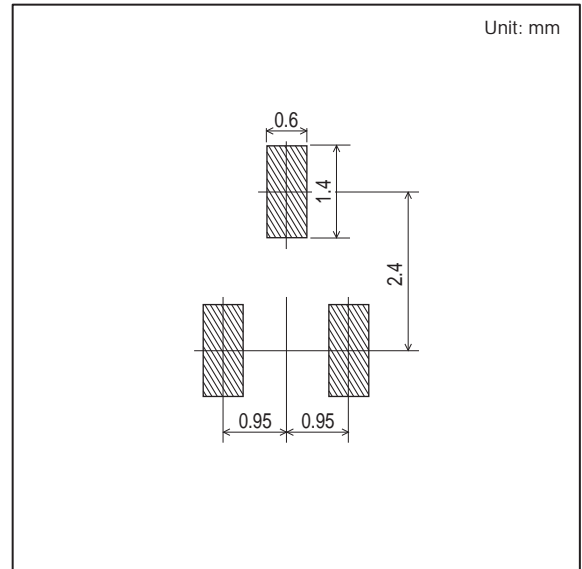
Those with one electrode terminal on the feed hole side.....TL

Outline Drawing

CPH3140-TL-E, CPH3240-TL-E



Land Pattern Example



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